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FGY120T65SPD_F085

650V, 120A Field Stop Trench IGBT With Soft Fast Recovery Diode

Features

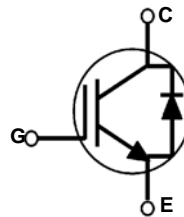
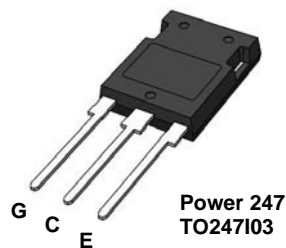
- Automotive Qualified
- Very low saturation voltage : $V_{CE(sat)} = 1.5 \text{ V(Typ.)} @ I_C = 120 \text{ A}$
- Maximum junction temperature : $T_J = 175 \text{ }^\circ\text{C}$
- Positive temperature Co-efficient
- Tight parameter distribution
- High input impedance
- 100% of the parts are dynamically tested
- Short circuit ruggedness $> 6 \mu\text{s} @ 25 \text{ }^\circ\text{C}$
- Copacked with soft, fast recovery Extremerfast diode

Benefits

- Very Low conduction and switching losses for a high efficiency operation in various applications
- Rugged transient reliability
- Outstanding parallel operation performance with balance current sharing
- Low EMI

Applications

- Traction inverter for HEV/EV
- Auxiliary DC/AC converter
- Motor drives
- Other power-train applications requiring high power switch



Absolute Maximum Ratings

Symbol	Description	Ratings	Units	
V_{CES}	Collector to Emitter Voltage	650	V	
V_{GES}	Gate to Emitter Voltage	± 20	V	
I_C	Collector Current (Note1)	@ $T_C = 25 \text{ }^\circ\text{C}$	240	A
	Collector Current	@ $T_C = 100 \text{ }^\circ\text{C}$	220	A
$I_{Nominal}$	Nominal Current	120	A	
I_{CM}	Pulsed Collector Current	378	A	
I_F	Diode Forward Current (Note1)	@ $T_C = 25 \text{ }^\circ\text{C}$	240	A
	Diode Forward Current	@ $T_C = 100 \text{ }^\circ\text{C}$	188	A
P_D	Maximum Power Dissipation	@ $T_C = 25 \text{ }^\circ\text{C}$	882	W
	Maximum Power Dissipation	@ $T_C = 100 \text{ }^\circ\text{C}$	441	W
SCWT	Short Circuit Withstand Time	@ $T_C = 25 \text{ }^\circ\text{C}$	6	μs
dV/dt	Voltage Transient Ruggedness (Note2)	10	V/ns	
T_J	Operating Junction Temperature	-55 to +175	$^\circ\text{C}$	
T_{stg}	Storage Temperature Range	-55 to +175	$^\circ\text{C}$	
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$	

Notes:

- 1: Limited by bondwire
- 2: $V_{CC} = 400 \text{ V}$, $V_{GE} = 15 \text{ V}$, $I_{CE} = 378 \text{ A}$, Inductive Load

FGY120T65SPD_F085 650V 120A Field Stop Trench IGBT With Soft Fast Recovery Diode

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance, Junction to Case	-	0.17	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$ (Diode)	Thermal Resistance, Junction to Case	-	0.32	$^{\circ}\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	$^{\circ}\text{C}/\text{W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Pacing Type	Qty per Tube
FGY120T65SPD	FGY120T65SPD_F085	TP-247	Tube	30ea

For Fairchild's definition of "green" Eco Status, please visit: http://www.fairchildsemi.com/company/green/rohs_green.html.

Electrical Characteristics of the IGBT $T_J = 25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0\text{V}, I_C = 1\text{mA}$	650	-	-	V
$\Delta BV_{CES} / \Delta T_J$	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{V}, I_C = 1\text{mA}$	-	0.6	-	$\text{V}/^{\circ}\text{C}$
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0\text{V}$	-	-	40	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0\text{V}$	-	-	± 250	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 120\text{mA}, V_{CE} = V_{GE}$	4.2	5.4	6.2	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 120\text{A}, V_{GE} = 15\text{V}$	-	1.5	1.85	V
		$I_C = 120\text{A}, V_{GE} = 15\text{V}, T_J = 175^{\circ}\text{C}$	-	1.8	-	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	-	6810	-	pF
C_{oes}	Output Capacitance		-	440	-	pF
C_{res}	Reverse Transfer Capacitance		-	50	-	pF
R_G	Internal Gate Resistance	$f = 1\text{MHz}$	-	3	-	Ω
Switching Characteristics						
$T_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{V}, I_C = 120\text{A}, R_G = 5\Omega, V_{GE} = 15\text{V}, \text{Inductive Load}, T_J = 25^{\circ}\text{C}$	-	53	-	ns
T_r	Rise Time		-	134	-	ns
$T_{d(off)}$	Turn-Off Delay Time		-	102	-	ns
T_f	Fall Time		-	115	-	ns
E_{on}	Turn-On Switching Loss		-	6.8	-	mJ
E_{off}	Turn-Off Switching Loss		-	3.5	-	mJ
E_{ts}	Total Switching Loss		-	10.3	-	mJ
$T_{d(on)}$	Turn-On Delay Time	$V_{CC} = 400\text{V}, I_C = 120\text{A}, R_G = 5\Omega, V_{GE} = 15\text{V}, \text{Inductive Load}, T_J = 175^{\circ}\text{C}$	-	50	-	ns
T_r	Rise Time		-	133	-	ns
$T_{d(off)}$	Turn-Off Delay Time		-	109	-	ns
T_f	Fall Time		-	138	-	ns
E_{on}	Turn-On Switching Loss		-	9.8	-	mJ
E_{off}	Turn-Off Switching Loss		-	4.0	-	mJ
E_{ts}	Total Switching Loss		-	13.8	-	mJ

Electrical Characteristics of the IGBT (Continued)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Units
Q_g	Total Gate Charge	$V_{CE} = 400V, I_C = 120A,$ $V_{GE} = 15V$	-	162	243	nC
Q_{ge}	Gate to Emitter Charge		-	49	-	nC
Q_{gc}	Gate to Collector Charge		-	47	-	nC

Electrical Characteristics of the Diode $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Units	
V_{FM}	Diode Forward Voltage	$I_F = 120A$	$T_J = 25\text{ }^\circ\text{C}$	-	1.3	1.6	V
			$T_J = 175\text{ }^\circ\text{C}$	-	1.2	-	
E_{rec}	Reverse Recovery Energy	$V_{CE} = 400V, I_F = 120A,$ $di_F/dt = 1000A/\mu s$	$T_J = 25\text{ }^\circ\text{C}$	-	450	-	μJ
			$T_J = 175\text{ }^\circ\text{C}$	-	3000	-	
T_{rr}	Diode Reverse Recovery Time		$T_J = 25\text{ }^\circ\text{C}$	-	123	-	ns
			$T_J = 175\text{ }^\circ\text{C}$	-	240	-	
Q_{rr}	Diode Reverse Recovery Charge		$T_J = 25\text{ }^\circ\text{C}$	-	2.8	-	μC
			$T_J = 175\text{ }^\circ\text{C}$	-	12.2	-	

Typical Performance Characteristics

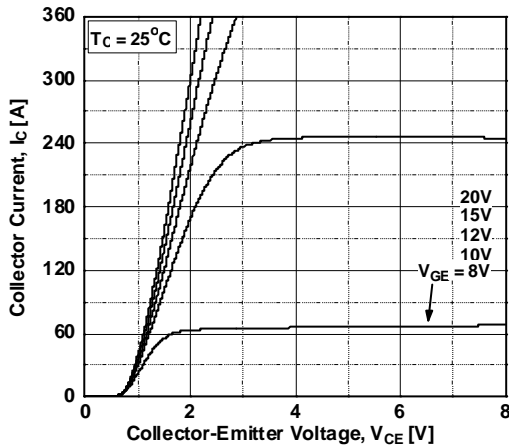


Figure 1. Typical Output Characteristics

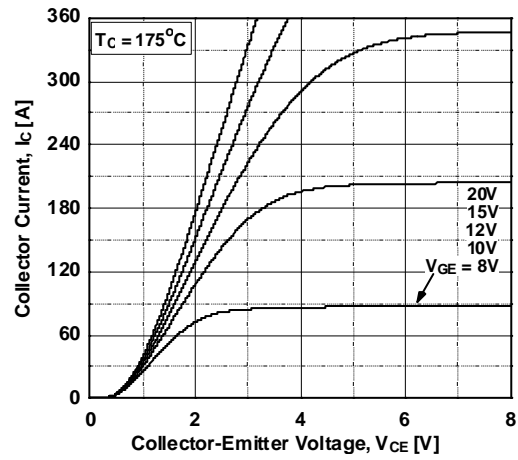


Figure 2. Typical Output Characteristics

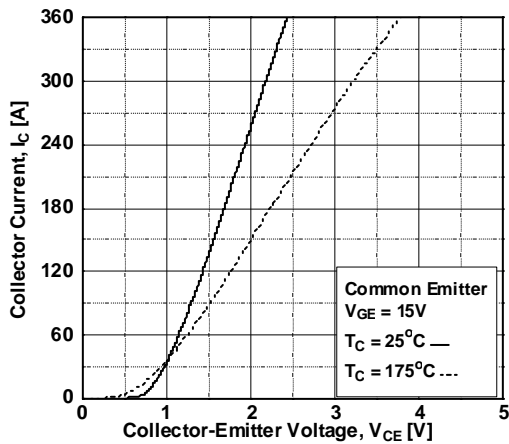


Figure 3. Typical Saturation Voltage Characteristics

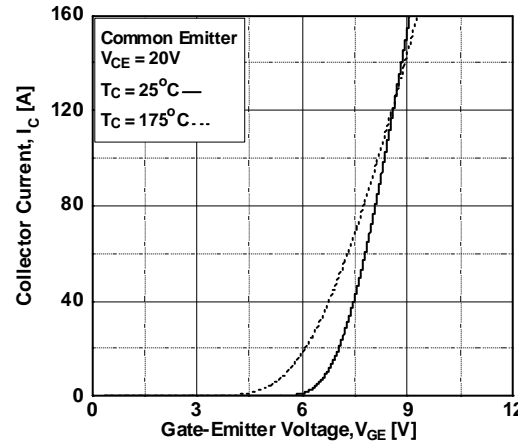


Figure 4. Transfer Characteristics

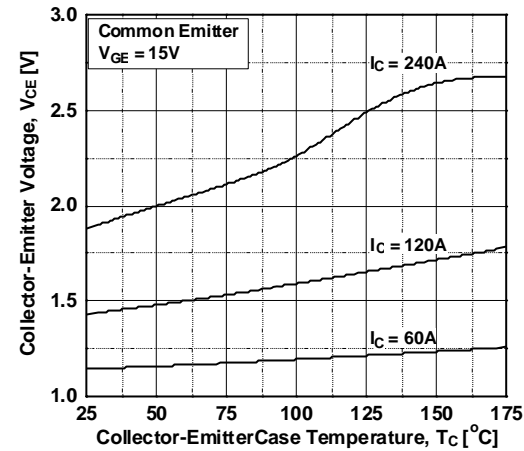


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

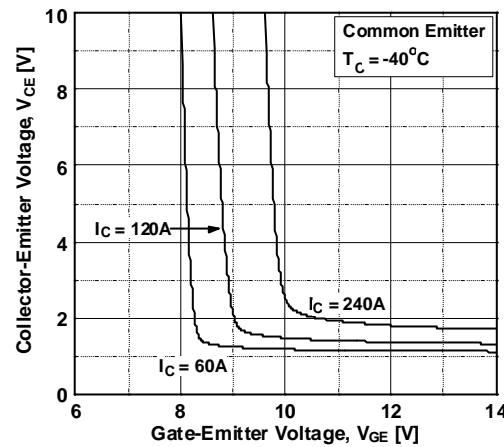


Figure 6. Saturation Voltage vs. V_{GE}

Typical Performance Characteristics

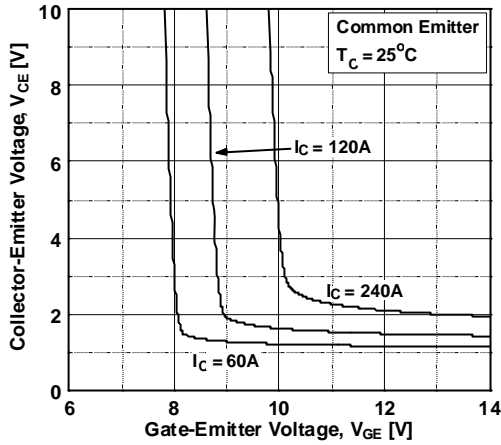


Figure 7. Saturation Voltage vs. V_{GE}

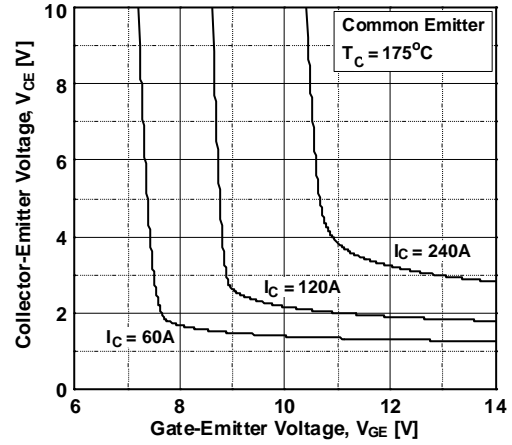


Figure 8. Saturation Voltage vs. V_{GE}

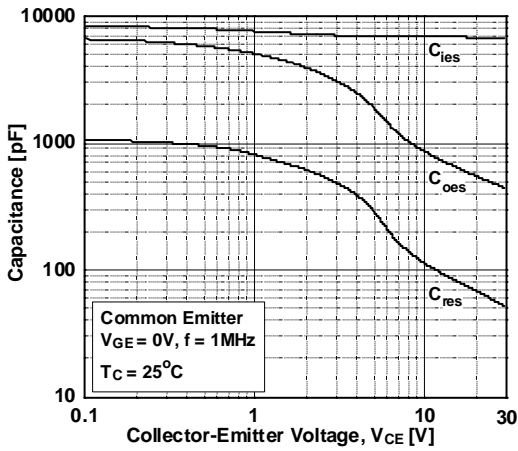


Figure 9. Capacitance Characteristics

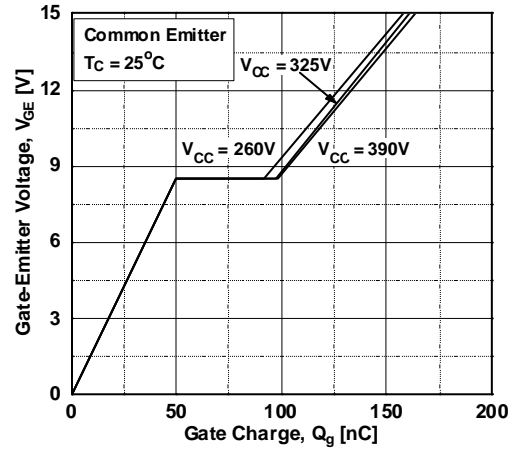


Figure 10. Gate charge Characteristics

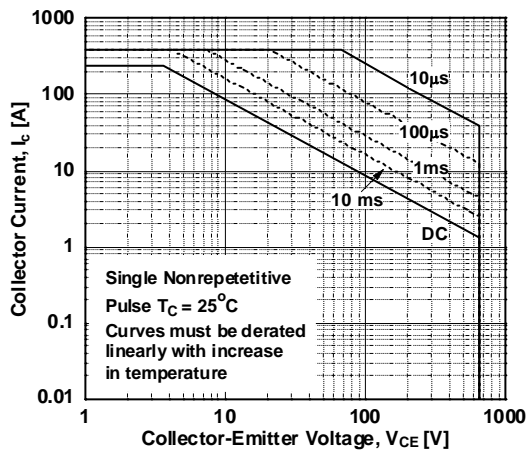


Figure 11. SOA Characteristics

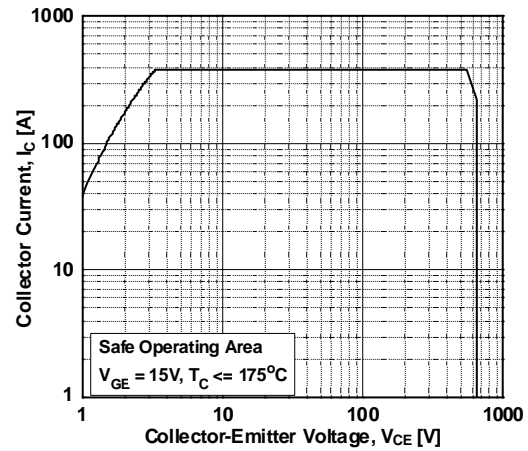


Figure 12. Turn off Switching SOA Characteristics

Typical Performance Characteristics

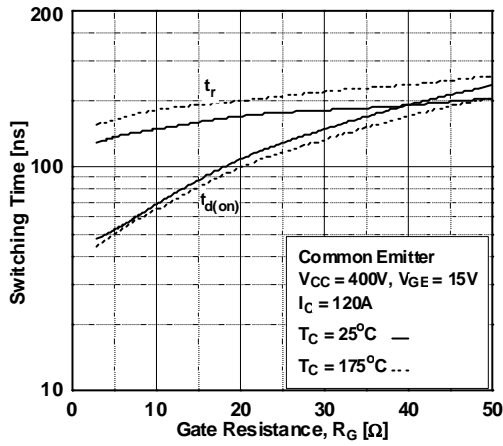


Figure 13. Turn-on Characteristics vs. Gate Resistance

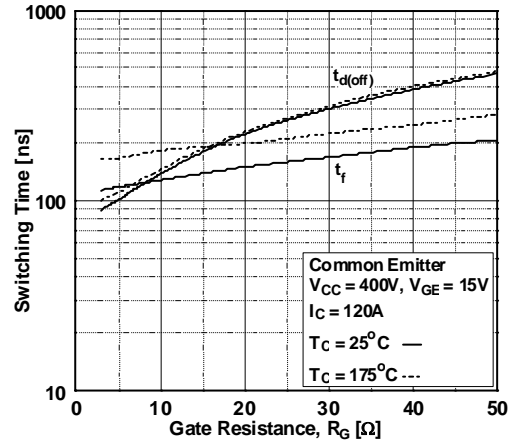


Figure 14. Turn-off Characteristics vs. Gate Resistance

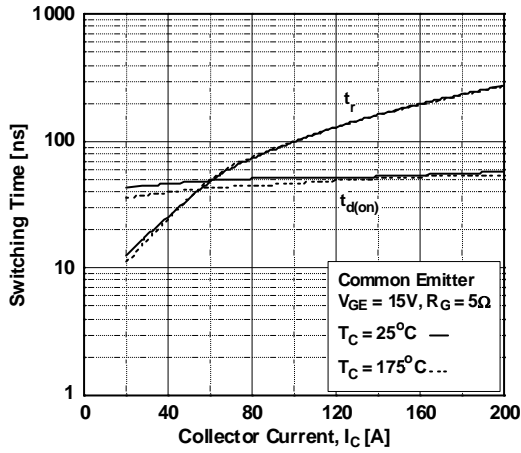


Figure 15. Turn-on Characteristics vs. Collector Current

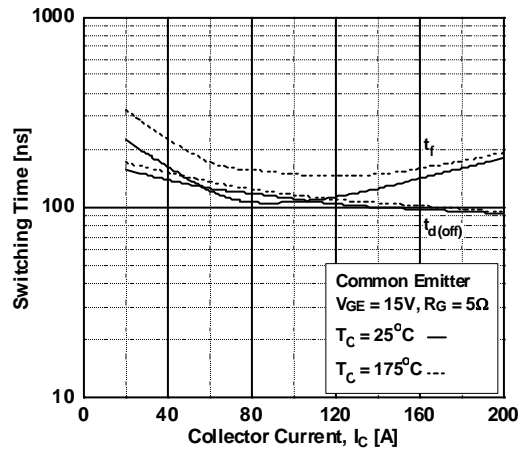


Figure 16. Turn-off Characteristics vs. Collector Current

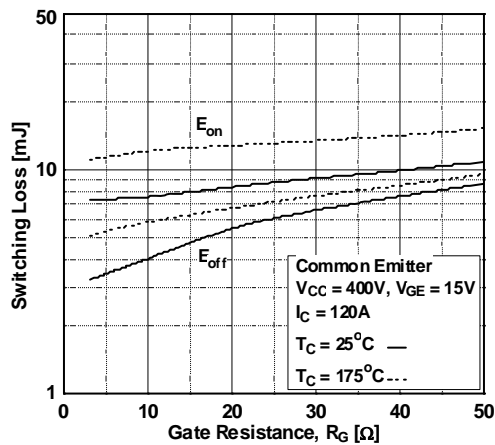


Figure 17. Switching Loss vs Gate Resistance

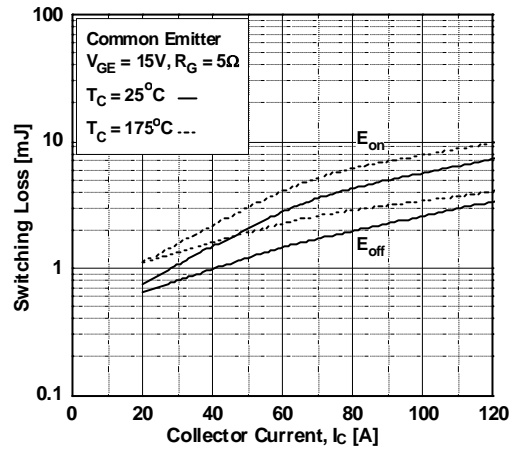


Figure 18. Switching Loss vs Collector Current

Typical Performance Characteristics

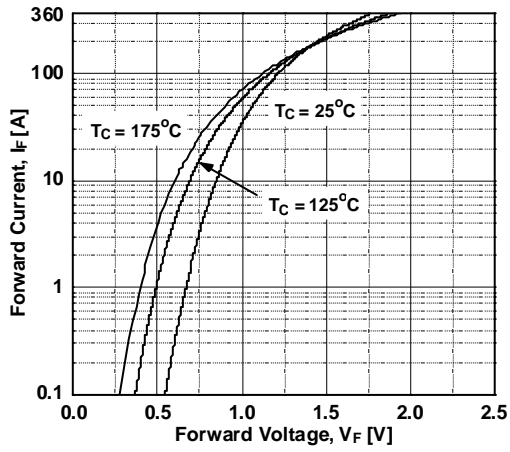


Figure 19. Forward Characteristics

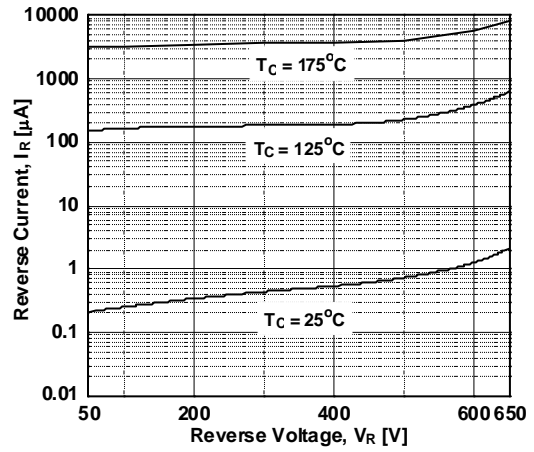


Figure 20. Reverse Current

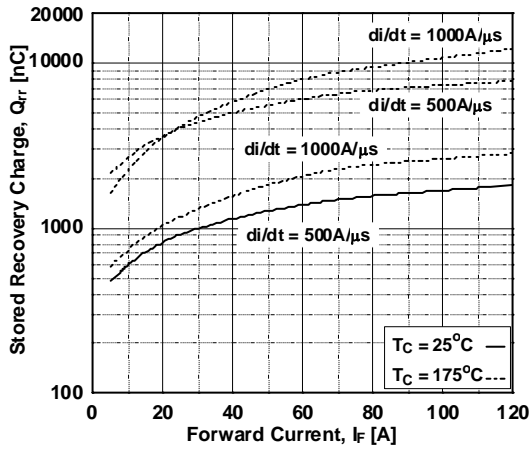


Figure 21. Stored Charge

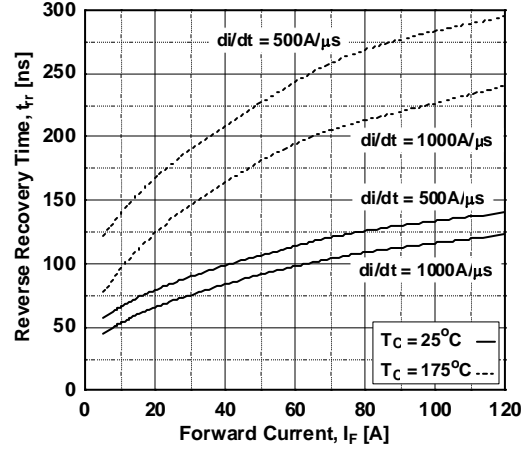


Figure 22. Reverse Recovery Time

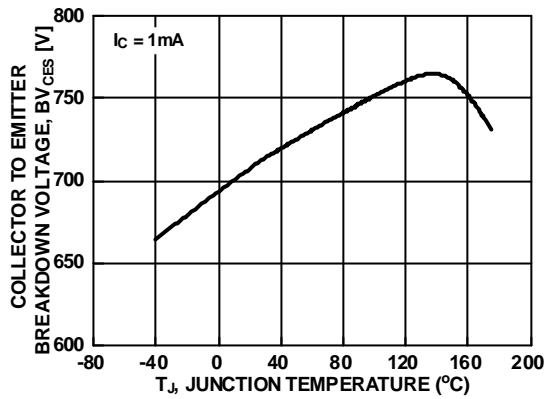


Figure 23. Collector to Emitter Breakdown Voltage vs. Junction Temperature

Typical Performance Characteristics

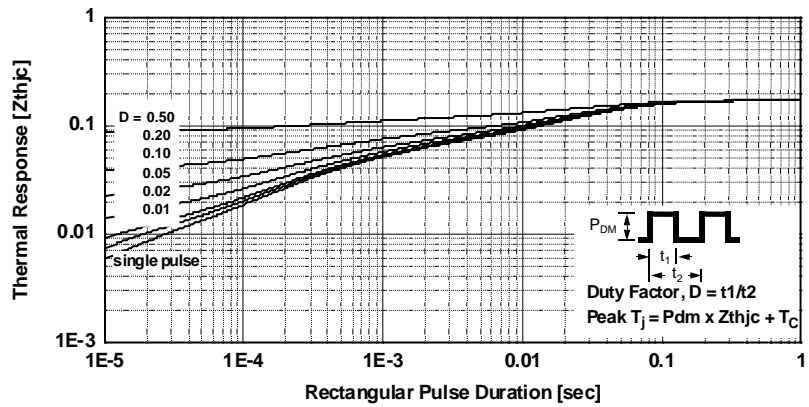


Figure 24. Transient Thermal Impedance of IGBT

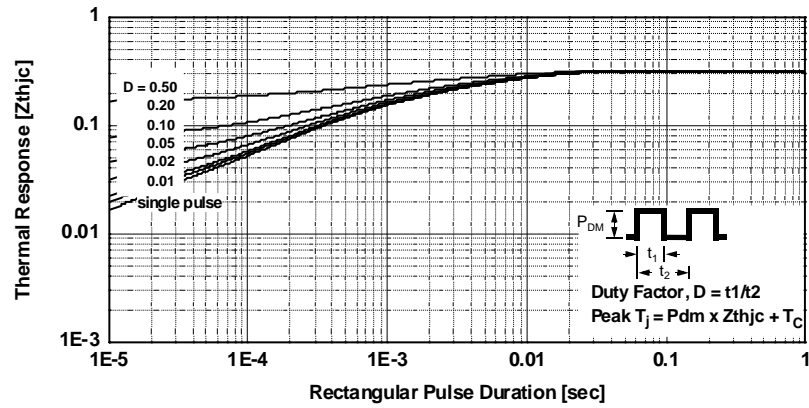
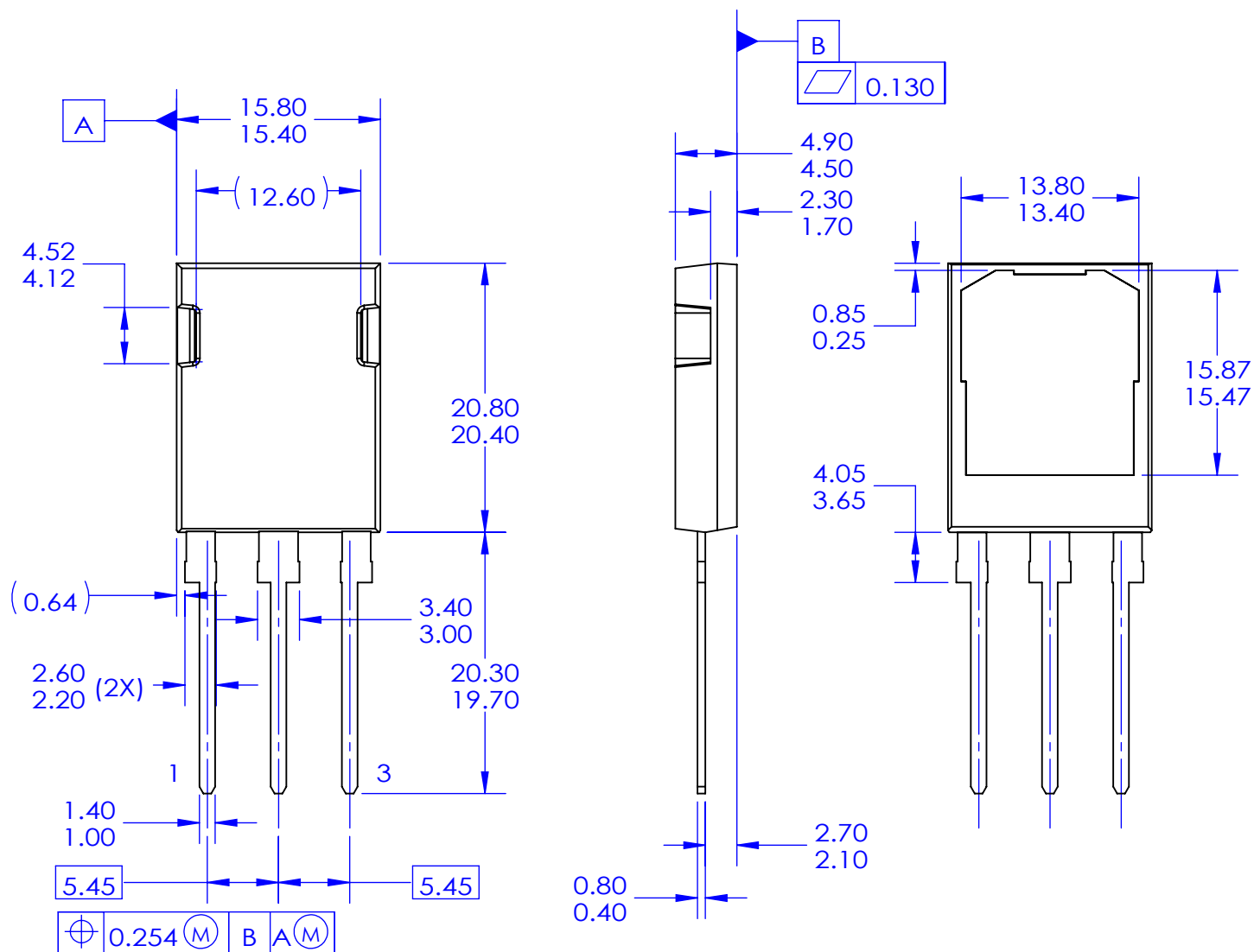


Figure 25. Transient Thermal Impedance of Diode



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